

/ Descriptions

WR0553I ММ Ё SQS æ Ñ ç s ll 1 Silicon PNP transistor in a TO-220F Plastic Package.

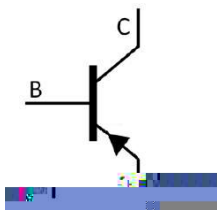
/ Features

к_{IH} 1 ó Ъ /ъ NWG5393 Ъ ´
Good Linearity of h_{FE} , complementary pair with KTD2060.

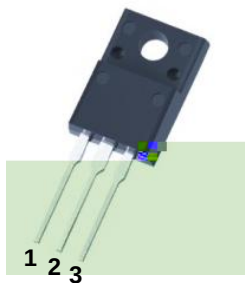
/ Applications

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General Purpose Application.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

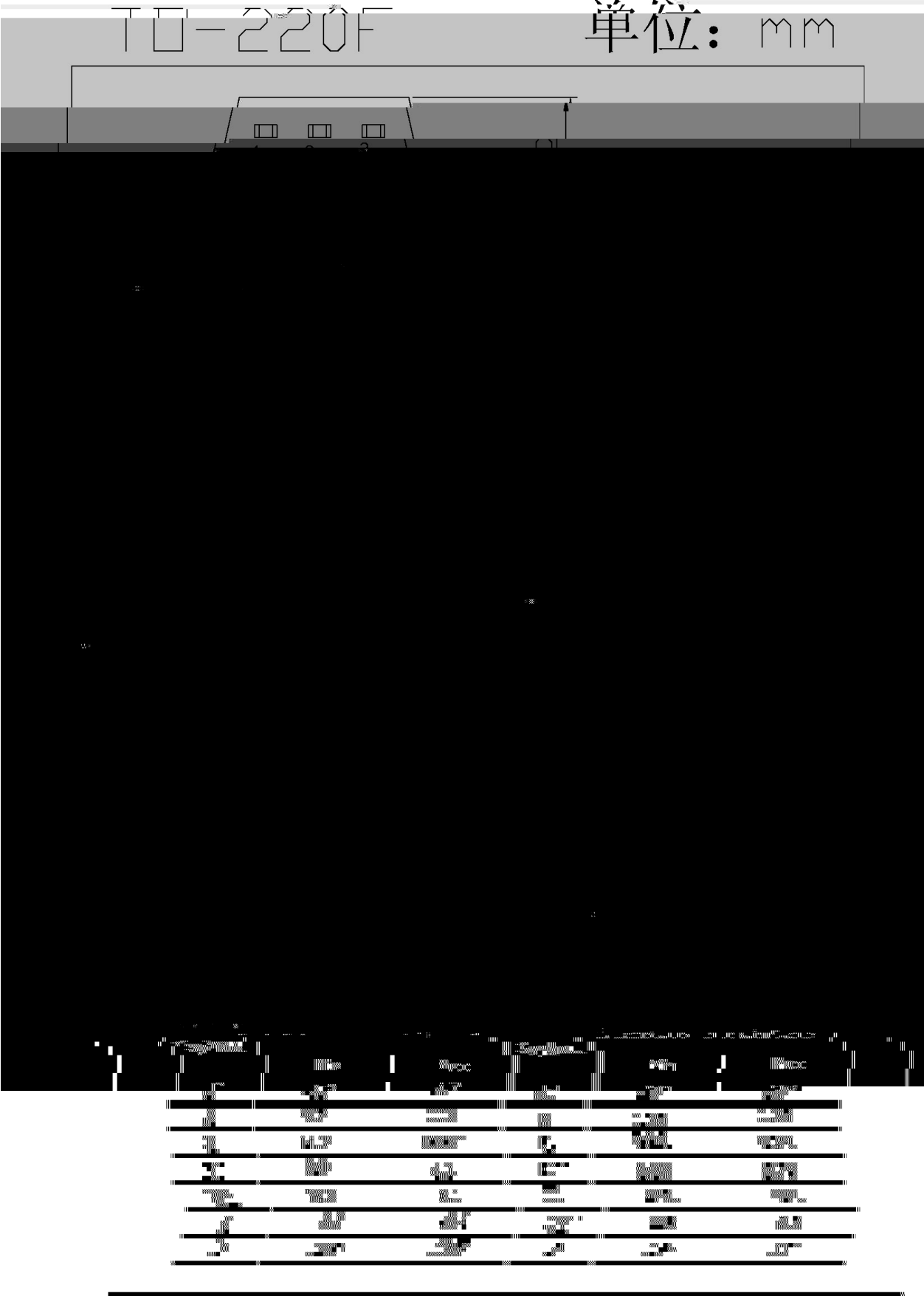
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	R	O	Y
h_{FE} Range	40~80	70~140	120~240

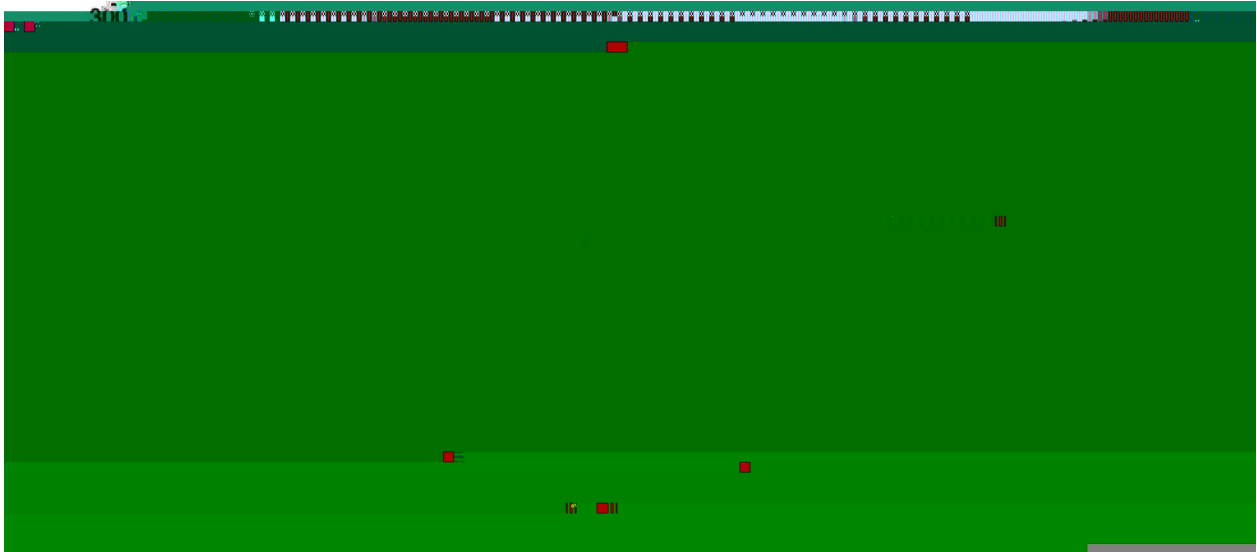
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-4	A
Base Current	I_B	-0.4	A
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	25	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 $\sim$ 150	$^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max
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/ Package Dimensions



() / Temperature Profile for Dip Soldering(Pb-Free)



б " X

1. 1. 25~150 °C, Time: 60~90sec;
2. 2. 255 °C, Duration: 5~0.5sec;
3. 3. Cooling Speed: 2~10 °C/sec.

Note:

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 255 °C, Duration: 5~0.5sec.
3. Cooling Speed: 2~10 °C/sec.